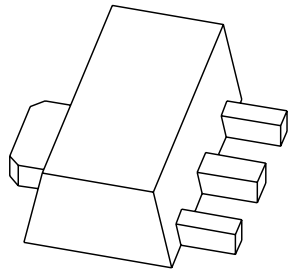


# DATA SHEET



**PBSS5480X**

80 V, 4 A

PNP low  $V_{CEsat}$  (BISS) transistor

Product specification  
Supersedes data of 2004 Jun 8

2004 Nov 08

# 80 V, 4 A PNP low $V_{CEsat}$ (BISS) transistor

## PBSS5480X

### FEATURES

- High  $h_{FE}$  and low  $V_{CEsat}$  at high current operation
- High collector current  $I_C$ : 4 A
- High efficiency leading to less heat generation.

### APPLICATIONS

- Medium power peripheral drivers (e.g. fans and motors)
- Strobe flash units for digital still cameras and mobile phones
- Inverter applications (e.g. TFT displays)
- Power switch for LAN and ADSL systems
- Medium power DC-to-DC conversion
- Battery chargers.

### DESCRIPTION

PNP low  $V_{CEsat}$  (BISS) transistor in a SOT89 (SC-62) plastic package.  
NPN complement: PBSS4480X.

### MARKING

TYPE NUMBER	MARKING CODE <sup>(1)</sup>
PBSS5480X	*1Z

### Note

- \* = p: made in Hong Kong.  
\* = t: made in Malaysia.  
\* = W: made in China.

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
$V_{CEO}$	collector-emitter voltage	-80	V
$I_C$	collector current (DC)	-4	A
$I_{CM}$	peak collector current	-10	A
$R_{CEsat}$	equivalent on-resistance	75	m $\Omega$

### PINNING

PIN	DESCRIPTION
1	emitter
2	collector
3	base

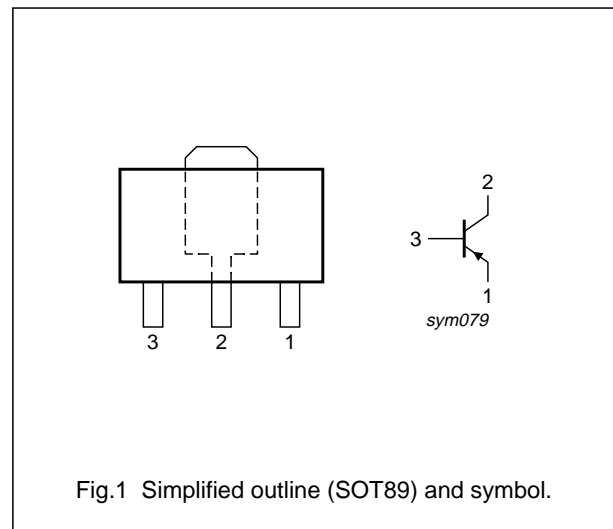


Fig.1 Simplified outline (SOT89) and symbol.

### ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PBSS5480X	SC-62	plastic surface mounted package; collector pad for good heat transfer; 3 leads	SOT89

80 V, 4 A  
PNP low  $V_{CEsat}$  (BISS) transistor

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**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

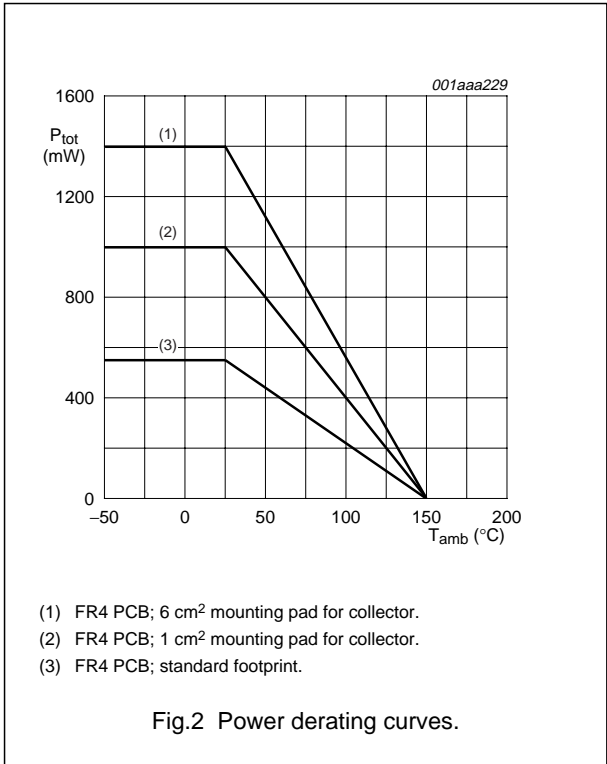
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	–80	V
$V_{CEO}$	collector-emitter voltage	open base	–	–80	V
$V_{EBO}$	emitter-base voltage	open collector	–	–5	V
$I_C$	collector current (DC)	note 1	–	–4	A
$I_{CM}$	peak collector current	$t_p \leq 1$ ms or limited by $T_{j(max)}$	–	–10	A
$I_{CRP}$	repetitive peak collector current	$t_p \leq 10$ ms; $\delta \leq 0.1$	–	–6	A
$I_B$	base current (DC)		–	–1	A
$I_{BM}$	peak base current	$t_p \leq 1$ ms	–	–2	A
$P_{tot}$	total power dissipation	$T_{amb} \leq 25$ °C notes 2 and 3 note 3 note 4 note 1 note 5	–	2.5 0.55 1 1.4 1.6	W W W W W
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C
$T_{amb}$	ambient temperature		–65	+150	°C

**Notes**

1. Device mounted on a printed-circuit board, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
2. Operated under pulsed conditions; pulse width  $t_p \leq 10$  ms; duty cycle  $\delta \leq 0.1$ .
3. Device mounted on a printed-circuit board, single-sided copper, tin-plated, standard footprint.
4. Device mounted on a printed-circuit board, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
5. Device mounted on a 7 cm<sup>2</sup> ceramic printed-circuit board, 1 cm<sup>2</sup> single-sided copper, tin-plated.

80 V, 4 A  
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# 80 V, 4 A PNP low $V_{CEsat}$ (BISS) transistor

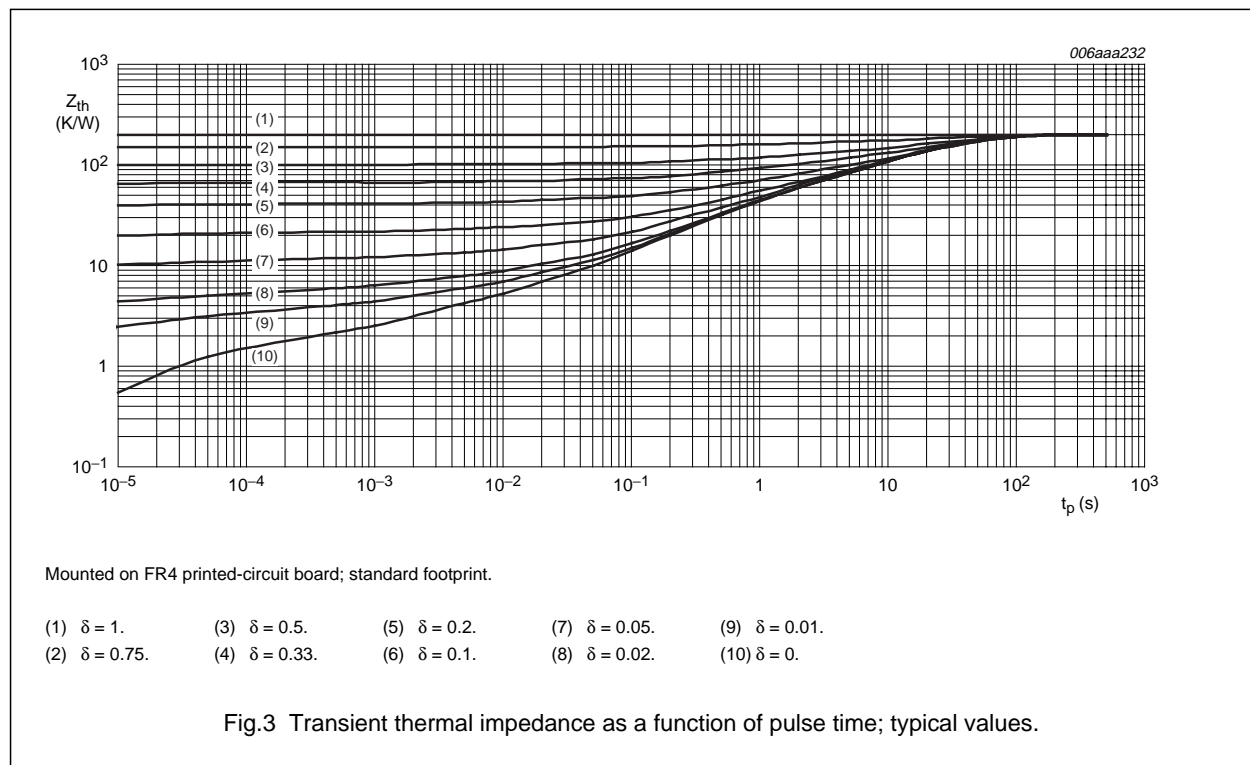
PBSS5480X

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		
		notes 1 and 2	50	K/W
		note 2	225	K/W
		note 3	125	K/W
		note 4	90	K/W
	note 5	80	K/W	
$R_{th(j-s)}$	thermal resistance from junction to soldering point		16	K/W

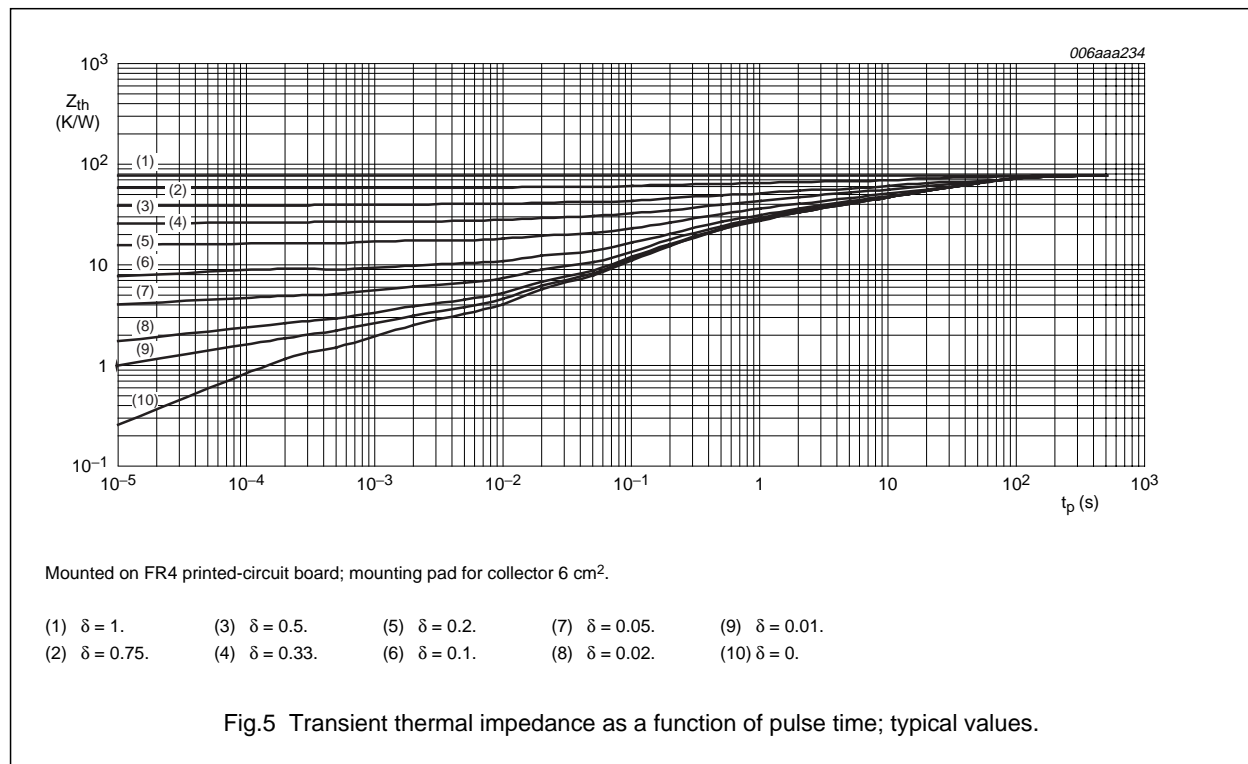
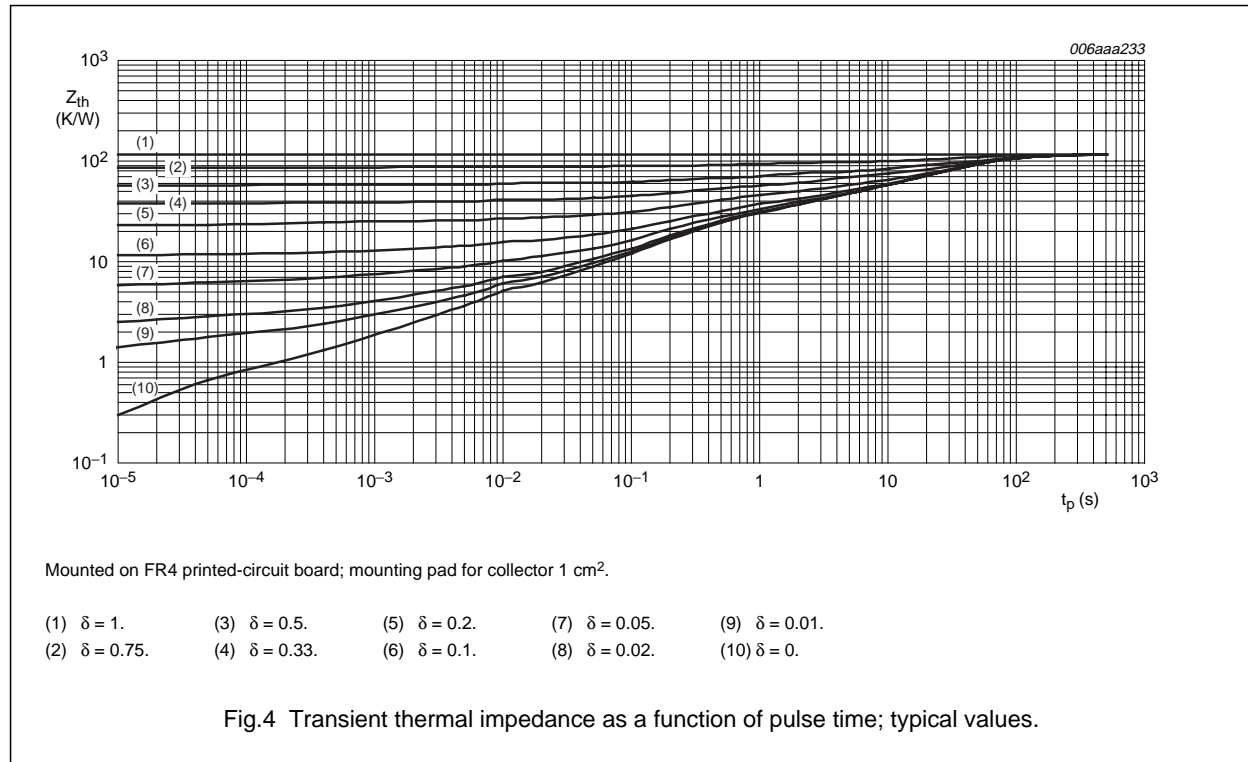
### Notes

1. Operated under pulsed conditions; pulse width  $t_p \leq 10$  ms; duty cycle  $\delta \leq 0.2$ .
2. Device mounted on a printed-circuit board, single-sided copper, tin-plated, standard footprint.
3. Device mounted on a printed-circuit board, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
4. Device mounted on a printed-circuit board, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
5. Device mounted on a 7 cm<sup>2</sup> ceramic printed-circuit board, 1 cm<sup>2</sup> single-sided copper, tin-plated.



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**CHARACTERISTICS** $T_{amb} = 25\text{ °C}$  unless otherwise specified.

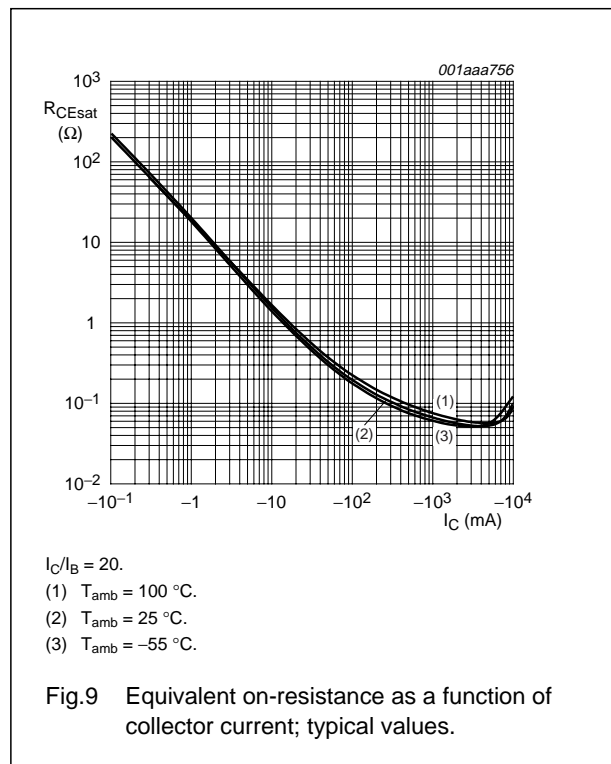
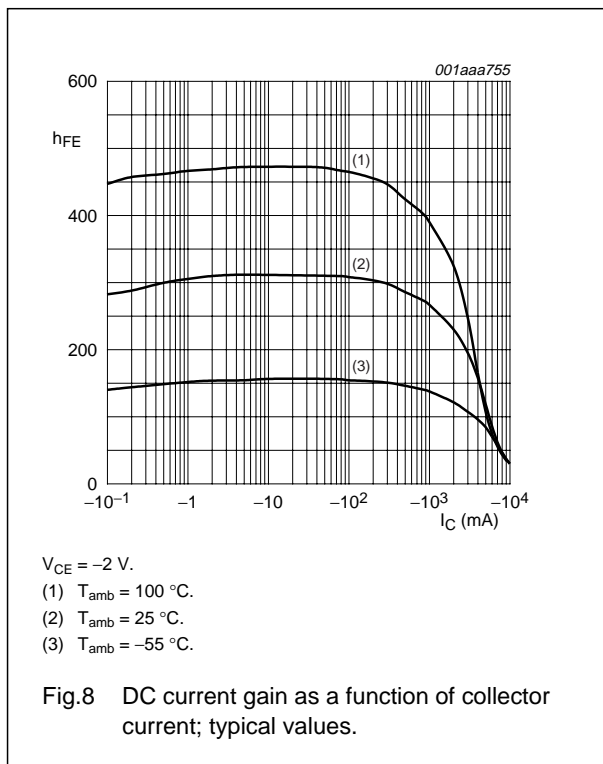
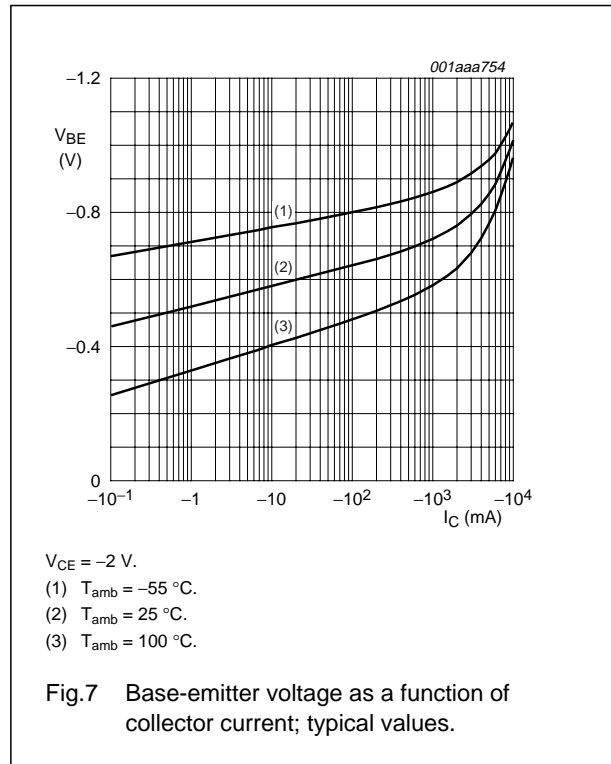
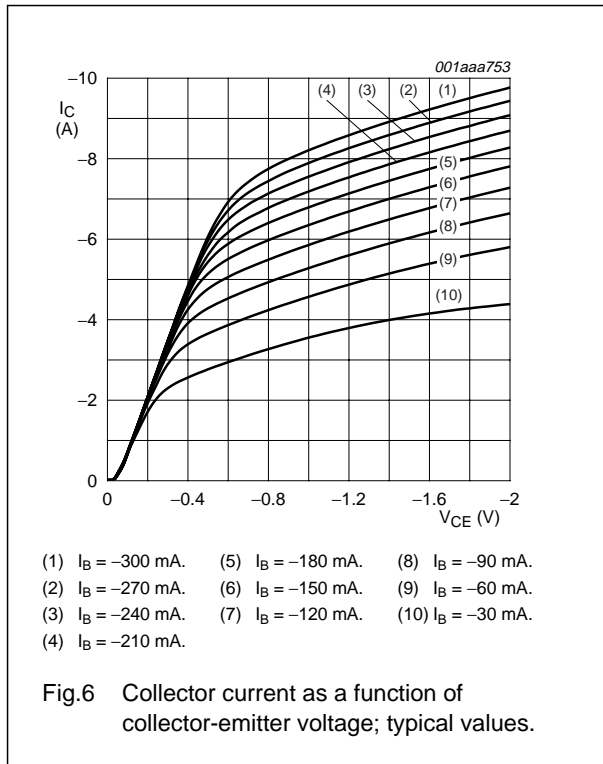
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CBO}$	collector-base cut-off current	$V_{CB} = -80\text{ V}; I_E = 0\text{ A}$	–	–	–100	nA
		$V_{CB} = -80\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ °C}$	–	–	–50	$\mu\text{A}$
$I_{CES}$	collector-emitter cut-off current	$V_{CE} = -60\text{ V}; V_{BE} = 0\text{ V}$	–	–	–100	nA
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = -5\text{ V}; I_C = 0\text{ A}$	–	–	–100	nA
$h_{FE}$	DC current gain	$V_{CE} = -2\text{ V}; I_C = -0.5\text{ A}$	200	300	–	
		$V_{CE} = -2\text{ V}; I_C = -1\text{ A}; \text{note 1}$	180	280	–	
		$V_{CE} = -2\text{ V}; I_C = -2\text{ A}; \text{note 1}$	150	240	–	
		$V_{CE} = -2\text{ V}; I_C = -4\text{ A}; \text{note 1}$	80	150	–	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = -0.5\text{ A}; I_B = -50\text{ mA}$	–	–35	–55	mV
		$I_C = -1\text{ A}; I_B = -50\text{ mA}$	–	–70	–105	mV
		$I_C = -2\text{ A}; I_B = -40\text{ mA}$	–	–170	–250	mV
		$I_C = -4\text{ A}; I_B = -200\text{ mA}; \text{note 1}$	–	–220	–340	mV
		$I_C = -5\text{ A}; I_B = -500\text{ mA}; \text{note 1}$	–	–250	–380	mV
$R_{CEsat}$	equivalent on-resistance	$I_C = -5\text{ A}; I_B = -500\text{ mA}; \text{note 1}$	–	50	75	$\text{m}\Omega$
$V_{BEsat}$	base-emitter saturation voltage	$I_C = -0.5\text{ A}; I_B = -50\text{ mA}$	–	–770	–850	mV
		$I_C = -1\text{ A}; I_B = -50\text{ mA}$	–	–810	–900	mV
		$I_C = -1\text{ A}; I_B = -100\text{ mA}; \text{note 1}$	–	–810	–900	mV
		$I_C = -4\text{ A}; I_B = -400\text{ mA}; \text{note 1}$	–	–930	–1000	mV
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = -2\text{ V}; I_C = -2\text{ A}$	–	–760	–850	mV
$f_T$	transition frequency	$I_C = -0.1\text{ A}; V_{CE} = -10\text{ V};$ $f = 100\text{ MHz}$	100	125	–	MHz
$C_c$	collector capacitance	$V_{CB} = -10\text{ V}; I_E = I_e = 0\text{ A};$ $f = 1\text{ MHz}$	–	60	90	pF

**Note**

1. Pulse test:  $t_p \leq 300\text{ }\mu\text{s}$ ;  $\delta \leq 0.02$ .

80 V, 4 A  
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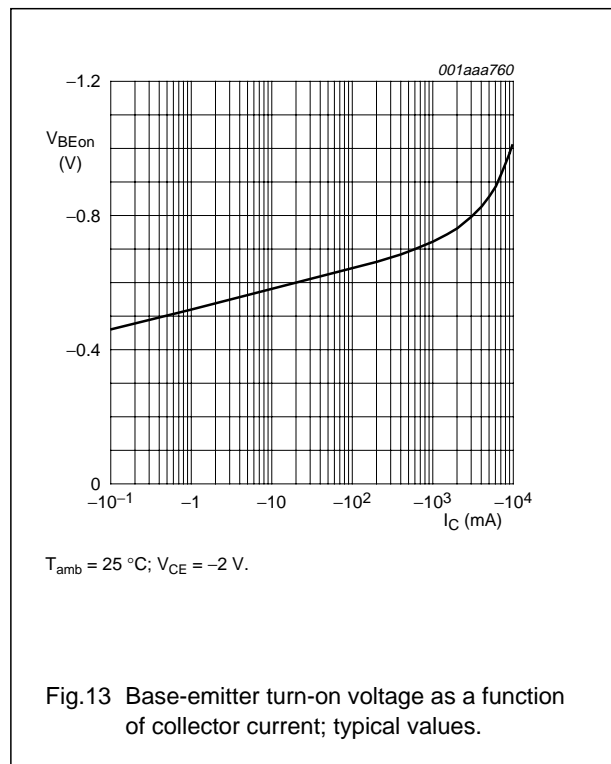
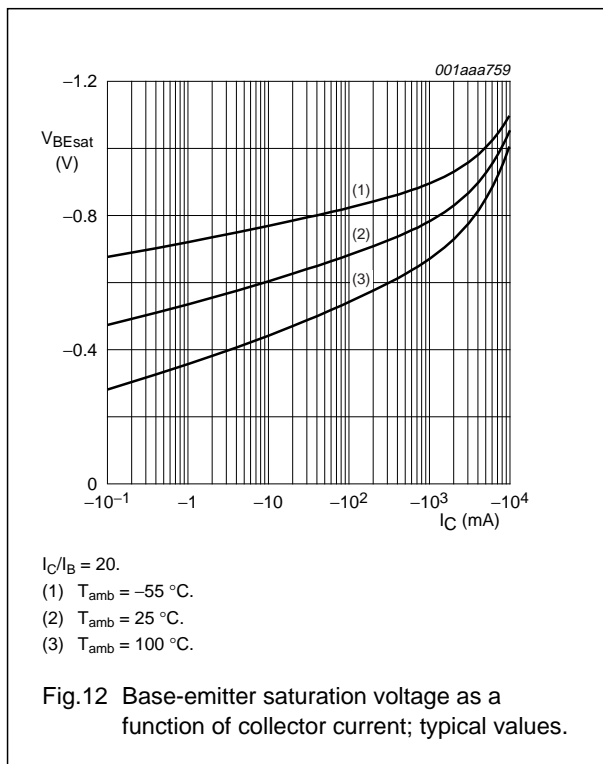
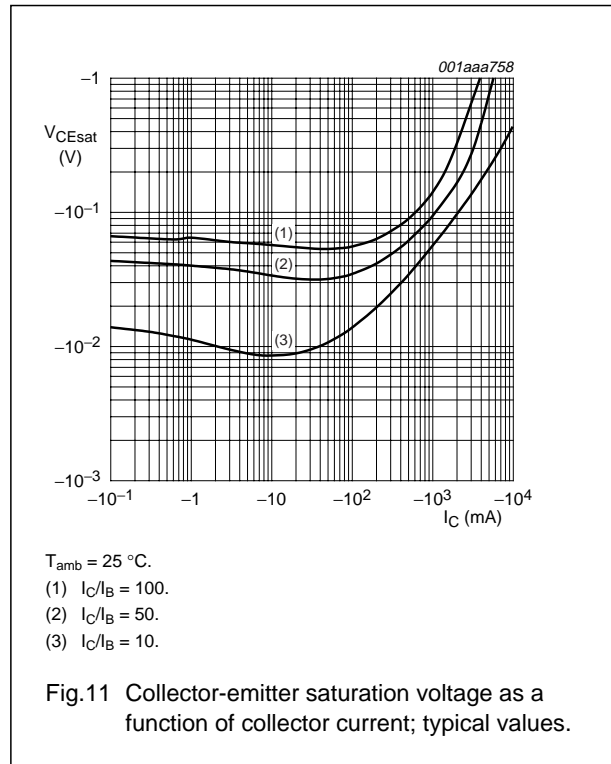
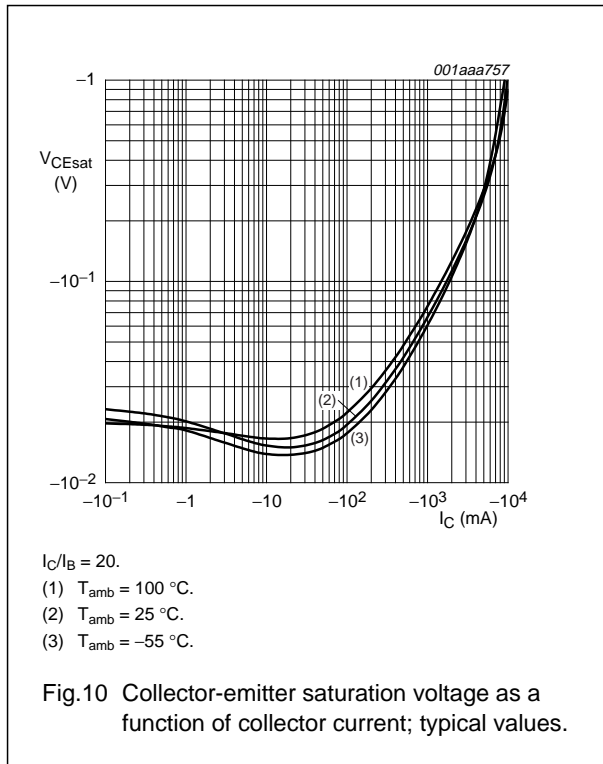
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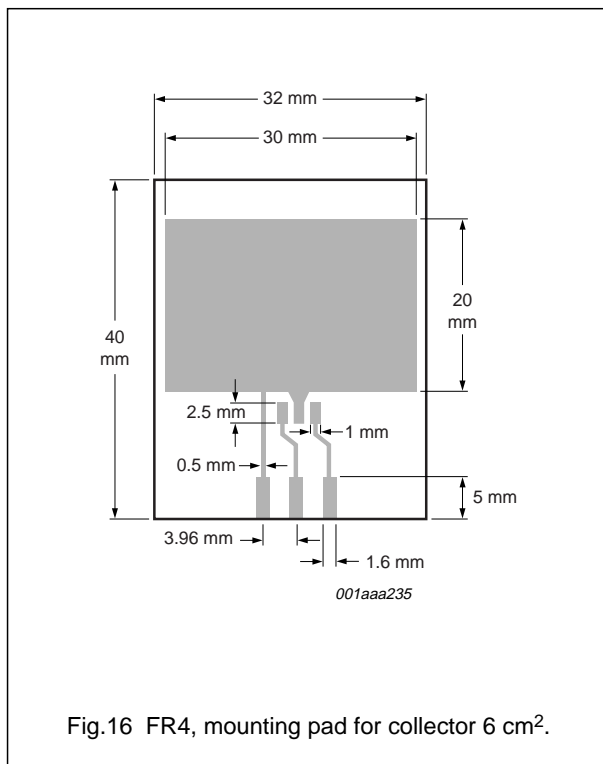
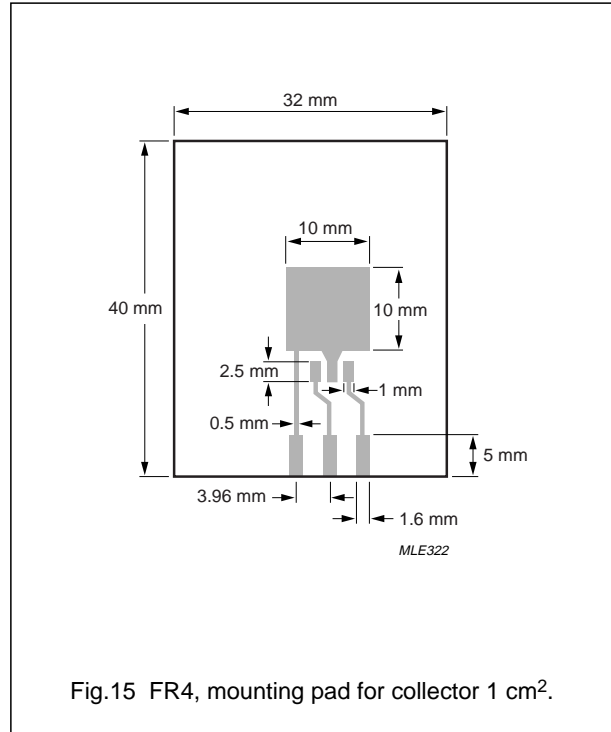
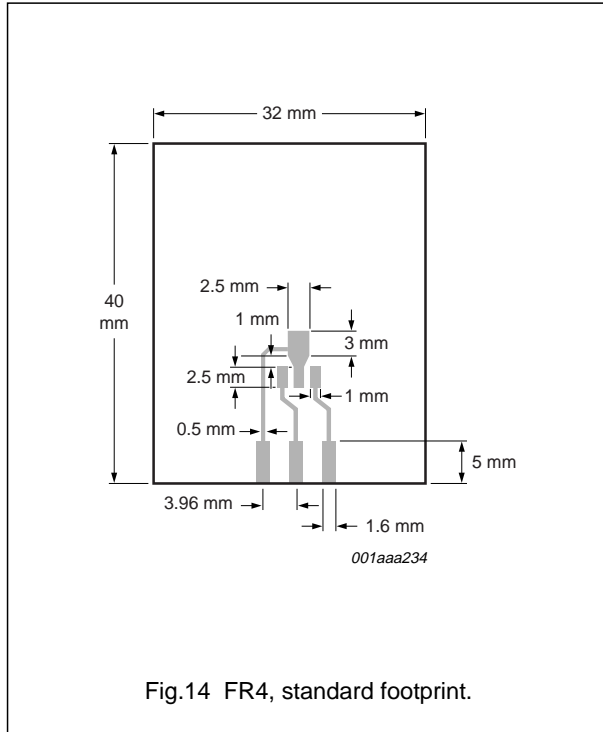
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Reference mounting conditions



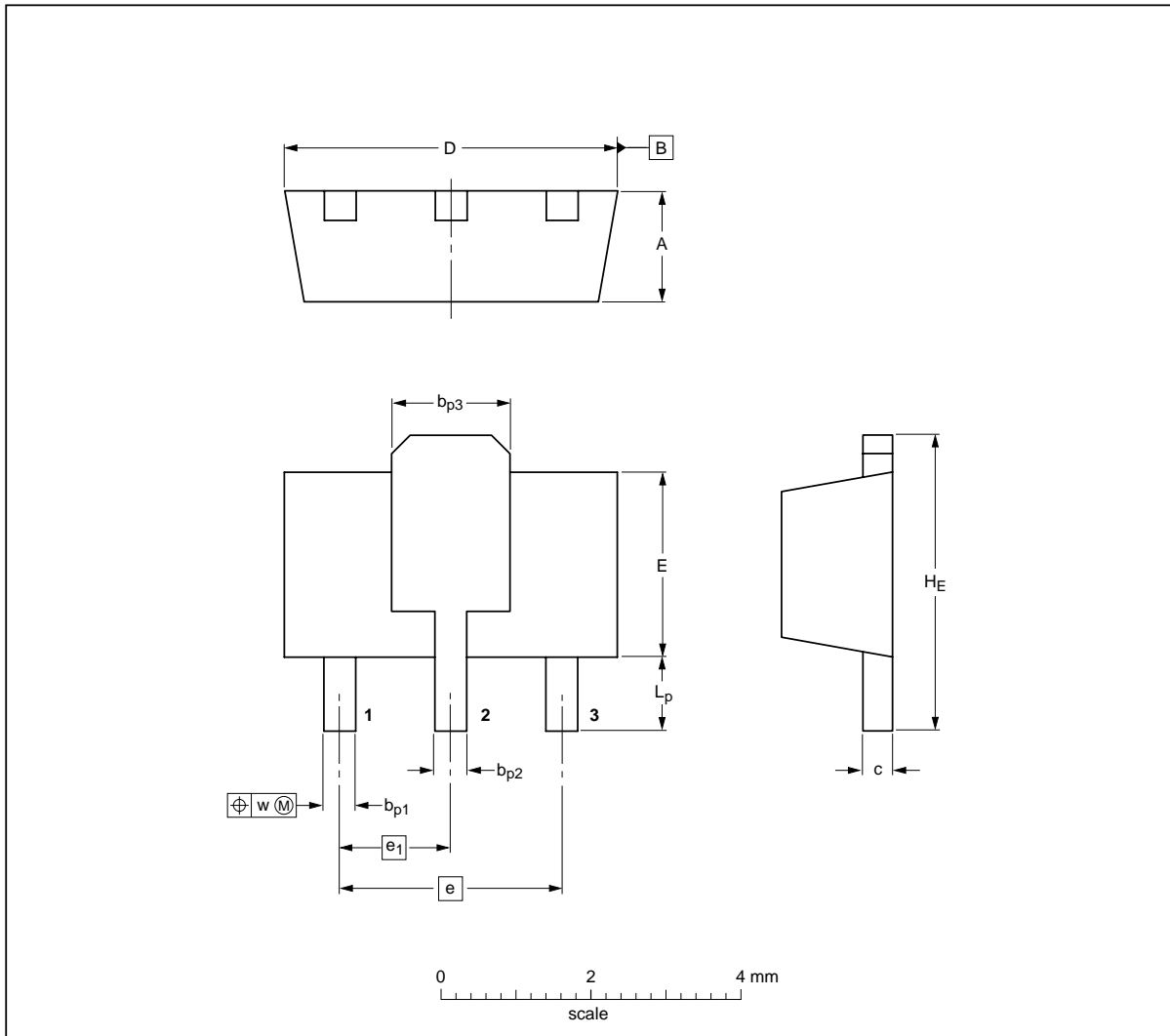
80 V, 4 A  
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PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 3 leads

SOT89



DIMENSIONS (mm are the original dimensions)

UNIT	A	b <sub>p1</sub>	b <sub>p2</sub>	b <sub>p3</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	w
mm	1.6 1.4	0.48 0.35	0.53 0.40	1.8 1.4	0.44 0.23	4.6 4.4	2.6 2.4	3.0	1.5	4.25 3.75	1.2 0.8	0.13

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT89		TO-243	SC-62		99-09-13 04-08-03

# 80 V, 4 A PNP low $V_{CEsat}$ (BISS) transistor

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## DATA SHEET STATUS

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